

## 144 nA I<sub>Q</sub> Low Quiescent Current Buck DC/DC Converter for Energy Harvester

No. EA-414-200508

#### **OVERVIEW**

R1800K is a power-storing buck DC/DC converter for a photovoltaic and vibration energy harvester. A low operating quiescent current allows a harvester to be used under a low-illumination environment, and it is suitable for an equipment with low power supplied from a harvester.

#### **KEY BENEFITS**

- Providing a low operating quiescent current (I<sub>Q</sub> 144 nA) and a high efficiency (approximately 90%@10 μA).
- A Control function that enables a maximum power optimizes a power supply from an energy harvester.

#### KEY SPECIFICATIONS

- Input Voltage Range: 2.0 V to 5.5 V
- Output Voltage Range: 2.0 V to 4.5 V
- Output Voltage Accuracy: ±3.0%
- Operating Quiescent Current: Typ.144 nA (Ta = 25°C, at no load)
- Starting Power: 720 nW
- Reverse Current Protection ( $V_{IN} \ge 2.0 \text{ V}$ )
- Accuracy of Maximum Power Voltage: 200 mV

APPLICATIONS

 Energy harvesting module of a photovoltaic and vibration energy harvester

PACKAGE



#### **SELECTION GUIDE**

Product Name	Package	Quantity per Reel
R1800KxxxA-TR	DFN(PL)2730-12	5,000 pcs

xxx: Select the ideal combination of the set output voltage (V<sub>SET</sub>) and the set maximum power voltage (V<sub>MPSET</sub>) from the code number starting from 002.

#### **TYPICAL CHARACTERISTICS**









No. EA-414-200508

## **SELECTION GUIDE**

The set output voltage and set maximum power voltage are user-selectable options.

#### **Selection Guide**

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R1800KxxxA-TR	DFN(PL)2730-12	5,000 pcs	Yes	Yes

xxx: Select the ideal combination of the set output voltage ( $V_{\text{SET}}$ ) and

the set maximum power voltage (V<sub>MPSET</sub>) from the code number starting from 002.

Output voltage: 2.0 V to 4.5 V in 0.1 V step

Maximum power voltage: 2.0 V to 5.3 V in 0.1 V step

# **BLOCK DIAGRAM**



R1800K Block Diagram

No. EA-414-200508

## **PIN DESCRIPTION**



#### DFN(PL)2730-12 Pin Description

Pin No.	Symbol	Description	
1	AGND	AGND Pin	
2	TEST1	Pin for Testing (Must not be connected)	
3	TEST2	Pin for Testing (Must not be connected)	
4	VM	Pin for Testing (Must not be connected)	
5	NC	No Connection (Must not be connected)	
6	NC	No Connection (Must not be connected)	
7	VFB	Feedback Pin	
8	PGND	PGND Pin	
9, 10	LX	DC/DC Switching Pin	
11, 12	VIN	Pin for Connecting Photovoltaic Element	

<sup>&</sup>lt;sup>(1)</sup> The tab on the bottom of the package enhances thermal performance and is electrically connected to GND (substrate level). It is recommended that the tab be connected to the ground plane on the board, or otherwise be left floating.

No. EA-414-200508

# **ABSOLUTE MAXIMUM RATINGS**

#### Absolute Maximum Ratings

Absolute M	Absolute Maximum Ratings (GND = 0 V)					
Symbol	Parameter	Rating	Unit			
VIN	VIN Pin Voltage	-0.3 to 6.5	V			
Max		-0.3 to V <sub>IN</sub> +	V			
V <sub>LX</sub>	LX Pin Voltage	0.3	v			
Vvfb	VFB Pin Voltage	-0.3 to 6.5	V			
PD	Power Dissipation <sup>(1)</sup> [ DFN(PL)2730-12, JEDEC STD. 51-7 Test Land Pattern ]	1850	mW			
Tj	Junction Temperature Range	-40 to 85	°C			
Tstg	Storage Temperature Range	-55 to 125	°C			

#### **ABSOLUTE MAXIMUM RATINGS**

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

# **RECOMMENDED OPERATING CONDITIONS**

#### **Recommended Operating Conditions**

Symbol	Parameter	Rating	Unit
V <sub>IN</sub>	Input Voltage	2.0 to 5.5	V
Та	Operating Temperature Range	-40 to 85	°C

#### **RECOMMENDED OPERATING CONDITIONS**

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

<sup>&</sup>lt;sup>(1)</sup> Refer to POWER DISSIPATION for detailed information.

No. EA-414-200508

# **ELECTRICAL CHARACTERISTICS**

The specifications surrounded by are guaranteed by design engineering at  $-40^{\circ}C \le Ta \le 85^{\circ}C$ .

R1800K E	Electrical Characteristics				(Ta	= 25°C)
Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Vout	Output Voltage	$V_{IN} \ge V_{SET} + 0.5 V$ , at no load	x 0.97		x 1.03	V
Ια	Operating Quiescent Current	$V_{IN} = 5.0 \text{ V},$ $V_{SET} = 3.0 \text{ V},$ device not switching		144	300	nA
Рѕт	Minimum Starting Power	Ta = 25°C, $V_{IN}$ = 4 V, $V_{SET}$ = 3.3 V, when constant current is applied		720		nW
V <sub>MP</sub>	Accuracy of Maximum Power Voltage				200	mV
Irev	Reverse Current	$V_{IN} \ge 2.0 \text{ V}, V_{FB} = 4.5 \text{ V}$ (When VIN drops from 2.5 V or more) Charging current to $C_{IN}$ and $C_{OUT}$ are not included <sup>(1)</sup>		10	100	nA

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj  $\approx$  Ta = 25°C). Test circuit is operated with "Open Loop Control" (GND = 0 V), unless otherwise specified.

<sup>&</sup>lt;sup>(1)</sup> Reverse current protection operates at V<sub>IN</sub> ≥ 2 V. It does not function with the voltage under 2 V. Set as V<sub>MPSET</sub> > V<sub>SET</sub> + 0.5 V. Due to having a hysteresis in the reverse current protection, a state may be detected as a reverse current even if  $V_{IN} = V_{OUT}$ .

No. EA-414-200508

The specifications surrounded by  $\square$  are guaranteed by design engineering at  $-40^{\circ}C \le Ta \le 85^{\circ}C$ .

#### **Product-specific Electrical Characteristics**

Product Name		<b>V</b> out <b>[V]</b>		V <sub>MP</sub> [V]		
Product Name	Min.	Тур.	Max.	Тур.	Max.	
R1800K002A	1.940	2.0	2.060	2.5	2.7	
R1800K003A	1.940	2.0	2.060	3.8	4.0	
R1800K004A	1.940	2.0	2.060	4.0	4.2	
R1800K005A	1.940	2.0	2.060	4.5	4.7	
R1800K006A	1.940	2.0	2.060	5.0	5.2	
R1800K008A	3.201	3.3	3.399	3.8	4.0	
R1800K009A	3.201	3.3	3.399	4.0	4.2	
R1800K010A	3.201	3.3	3.399	4.5	4.7	
R1800K011A	3.201	3.3	3.399	5.0	5.2	
R1800K014A	4.365	4.5	4.635	5.0	5.2	
R1800K016A	3.783	3.9	4.017	4.4	4.6	
R1800K019A	2.910	3.0	3.090	4.4	4.6	
R1800K020A	2.910	3.0	3.090	4.2	4.4	
R1800K021A	2.619	2.7	2.781	3.9	4.1	
R1800K022A	2.619	2.7	2.781	4.4	4.6	
R1800K023A	2.619	2.7	2.781	5.0	5.2	

No. EA-414-200508

## THEORY OF OPERATION

#### MAXIMUM POWER CONTROL



Intervals of the charge transfer to  $C_{\mbox{\scriptsize OUT}}$  by switching

R1800K transfers power to a secondary side at the maximum power voltage ( $V_{MP}$ ), which is the operating point of the maximum amount of power generation of a solar cell. After R1800K receives power from the solar cell, the input voltage increases and when it reaches the  $V_{MP}$ , a switching starts and the R1800K transfers power to the secondary side. When a power transfer amount exceeds the supplied power from the solar cell, the input voltage decreases by the switching. At a certain point, the switching stops and a state changes to a charging mode. When the input voltage reaches the  $V_{MP}$  again, the R1800K transfers power to the secondary side. By repeating this operation enables transferring power to the secondary side while maintaining the operating point of the maximum amount of power generation of the solar cell.

No. EA-414-200508

#### **REVERSE CURRENT DETECTION**



R1800K has a reverse current protection to maintain an electric charge of the output side when the light is cut off. When the light is cut off after a normal operation and a power supply from the solar cell is discontinued, the charge of supply current of a circuit connected respectively to the input and output sides is drawn. When the input voltage drops below the output voltage, the reverse current protection operates (at the backflow) and prevents the charge drawn from the output side. As shown in the figure above, this protection operates at 2 V or higher. When the input voltage drops below 2 V, the charge of the output side flows back to the input side. The drawn charge increases for a moment, but the R1800K returns to the reverse current protection state. The average amount of charge drawn from the output side is extremely minute.

No. EA-414-200508

# **APPLICATION INFORMATION**

#### **Typical Application Circuit**



**R1800K Typical Application Circuit** 

#### **Recommended External Components**

Symbol	Descriptions	Parts Name
CIN	Ceramic Capacitor 10 µF or higher	C1608X5R1E106M080AC
Carr	Ceramic Capacitor 47 µF or higher	C3216X6S1A476M160AC
Соит	Large-capacity Electrical Storage Device	Refer below table
L	Inductor 22 µH	VLS201612CX-220M-1

#### **Recommended Large-capacity Electrical Storage Devices**

Manufacturer	Series	Parts Name	Capacity	Туре	Supplement
ТДК	CeraCharge™	BCT1812M101AG	100µAh	All-solid-state	CeraCharge <sup>™</sup> is a trademark
IDK		BCTIOIZIMIUTAG	τουμΑπ	Li-ion	of TDK
NICHICON	SLB series	SLB03070LR35	350µAh	Li-ion	
NGK	EnerCera®	ET1210C-R ET2016C-R	5mAh 25mAh	Li-ion	EnerCera® is a trademark of
NGK	EnerCera®	ET2016C-R ET271704P-H	5mAh	LI-ION	NGK
Murata	CT series	CT04120	3mAh	Li-ion	

No. EA-414-200508

# **TECHNICAL NOTES**

The performance of a power source circuit using this device is highly dependent on a peripheral circuit. A peripheral component or the device mounted on PCB should not exceed a rated voltage, a rated current or a rated power. When designing a peripheral circuit, please be fully aware of the following points.

- External components must be connected as close as possible to the IC and make wiring as short as possible. Especially, the capacitor connected in between V<sub>IN</sub> pin and GND pin must be wiring the shortest.
- If their impedance is high, internal voltage of the IC may shift by the switching current, and the operating may be unstable. Make the power supply and GND lines sufficient.
- As for wirings of the power, the ground, the inductor, the LX and the VFB pins, due consideration must be given to large current occurred by switching.
- Using a ceramic capacitor with a lower equivalent series resistance (ESR) is recommended; a capacitor of 10μF or higher for C<sub>IN</sub> between V<sub>IN</sub> and GND pins, a capacitor of 47μF or higher for C<sub>OUT</sub>. Using a mass-storage device for C<sub>OUT</sub> also is recommended. Please choose capacitors depending on the bias characteristics, V<sub>IN</sub> and V<sub>OUT</sub>. (Refer to *Recommended External Components*)
- Please choose inductors which have low direct-current resistance, enough allowable current and low magnetic saturation. Current-limited circuit may operate with LX peak current before reaching expected load current in case of low allowable current and extremely low inductance value under load condition.
- Note that the current-limited circuit is self-heating and radiation environment sensitive.

No. EA-414-200508

## • PCB Layout

R1800KxxxA-TR (PKG:DFN(PL)2730-12)





No. EA-414-200508

# **TYPICAL CHARACTERISTICS**

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

Vin= 4 V

Vin= 5 V

1500

Vin= 4.5 V

2000



#### 3) Output Voltage vs. Output Current

500

1000

Output Current (uA)

3.35

3.3

3

0

3.3 3.25 3.25 3.15 3.15 3.15 3.05 3.05 3.05







# POWER DISSIPATION

# DFN(PL)2730-12

Ver. A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

ltem	Measurement Conditions	
Environment	Mounting on Board (Wind Velocity = 0 m/s)	
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)	
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm	
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square	
Through-holes	φ 0.3 mm × 23 pcs	

#### **Measurement Result**

(Ta = 25°C, Tjmax = 85°C)

Item	Measurement Result
Power Dissipation	1850 mW
Thermal Resistance (θja)	θja = 32°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 8°C/W

 $\theta$ ja: Junction-to-Ambient Thermal Resistance

wjt: Junction-to-Top Thermal Characterization Parameter





Power Dissipation vs. Ambient Temperature

Measurement Board Pattern

# PACKAGE DIMENSIONS

DFN(PL)2730-12

Ver. A



DFN(PL)2730-12 Package Dimensions (Unit: mm)

<sup>\*</sup>The tab on the bottom of the package shown by blue circle is a substrate potential (GND). It is recommended that this tab be connected to the ground plane on the board but it is possible to leave the tab floating.

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